

ABRASIVE-FREE POLISHING SYSTEM

ABSTRACT

The invention provides a chemical-mechanical polishing system comprising a water-soluble silicate compound, an oxidizing agent that oxidizes at least a part of a substrate, water, and a polishing pad, wherein the polishing system is substantially free of abrasive particles. The invention further provides a method of chemically-mechanically polishing a substrate with the aforementioned polishing system. The polishing system is particularly useful in the removal of tantalum.

No Figure